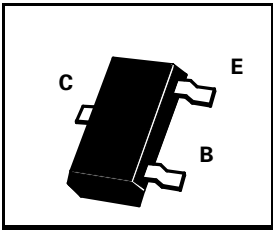


SOT23 PNP SILICON PLANAR SMALL SIGNAL TRANSISTOR

FMMT5087

PARTMARKING DETAIL - FMMT5087 - 2m
FMMT5087R - 3m

COMPLEMENTARY TYPE - FMMT5088



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-3	V
Continuous Collector Current	I_C	-100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Cut-Off Current	I_{CBO}		-10 -50	nA μA	$V_{CB}=-10V, I_E=0$ $V_{CB}=-35V, I_E=0$
Emitter-Base Current	I_{EBO}		-50	nA	$V_{EB}=-3V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-300	mV	$I_C=-10mA, I_B=-1mA$
Base-Emitter ON Voltage	$V_{BE(on)}$		-850	mV	$I_C=-1mA, V_{CE}=-5V$
Static Forward Current Transfer Ratio	h_{FE}	250 250 250	800		$I_C=-100\mu A, V_{CE}=-5V$ $I_C=-1mA, V_{CE}=-5V$ $I_C=-10mA, V_{CE}=-5V^*$
Transition Frequency	f_T	40		MHz	$I_C=-500\mu A, V_{CE}=-5V, f=20MHz$
Small Signal Current Transfer Ratio	h_{fe}	250	900		$I_C=-1mA, V_{CE}=-5V, f=1KHz$
Noise Figure	N		2	dB	$I_C=200\mu A, V_{CE}=-5V, R_g=2K\Omega$ $f=30Hz$ to $15KHz$ at 2dB points
Output Capacitance	C_{obo}		4	pF	$V_{CB}=-5V, f=140MHz, I_E=0$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device